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CERTIFICATE OF CORRECTION

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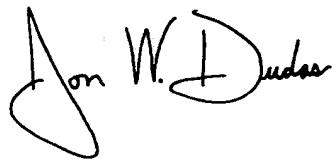
Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

The title page should be deleted and substitute therefor the attached title page as shown on the attached page.

Signed and Sealed this

Thirty-first Day of May, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office

(12) United States Patent
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(54) HETEROJUNCTION ORGANIC SEMICONDUCTOR FIELD EFFECT TRANSISTOR (FET) WITH A GATE INSULATION LAYER AND MANUFACTURING PROCESS THEREOF

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(58) Field of Search 257/40, 192, 77, 257/347, 613, 289, 66; 438/99, 151, 158, 161

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(57) ABSTRACT

A organic semiconductor field effect transistor that can work in the depletion mode or super-inverse mode, comprising: a substrate (1), a gate electrode (2) formed on the substrate (1), a gate insulation layer (3) formed on the substrate (1) and the gate electrode (2), a first semiconductor layer (4) formed on the gate insulation layer (3), a source electrode and a drain electrode (5) formed on the first semiconductor layer (4), and a second semiconductor layer (6) formed on the first semiconductor layer (4) and the source/drain electrodes (5).

9 Claims, 5 Drawing Sheets

